

● FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

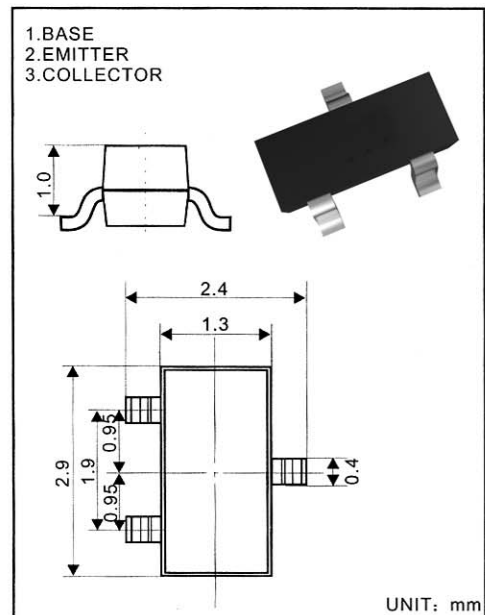
I_{CM} : 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 40V

Operating and storage junction temperature range

T_{j}, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



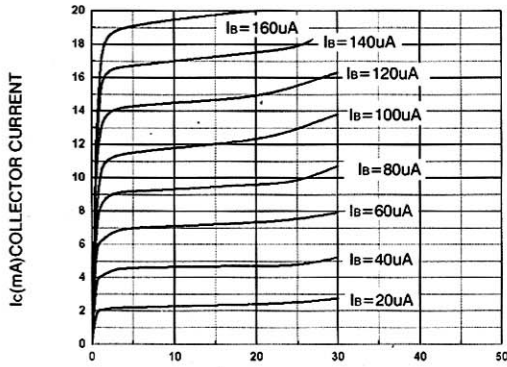
● ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

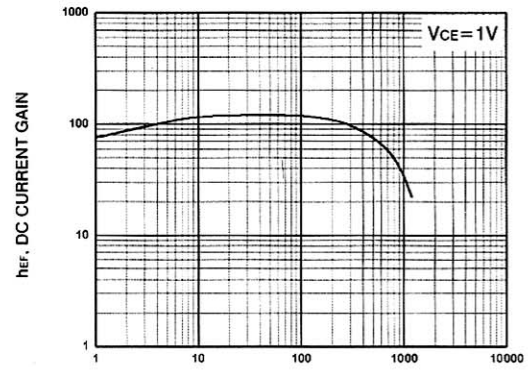
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=0.1mA, I_b=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_c=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
	I_{CEO}	$V_{CE}=20V, I_b=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_c=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_c=50mA$	120		350	
	$h_{FE(2)}$	$V_{CE}=1V, I_c=500mA$	40			
Collector-emitter saturation voltage	V_{CEsat}	$I_c=500mA, I_b=50mA$			0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_c=500mA, I_b=50mA$			1.2	V
Base-emitter voltage	V_{BEF}	$I_E=100mA$			1.4	V
Transition frequency	f_t	$V_{CE}=6V, I_c=20mA$ $f=30MHz$	150			MHz

● CLASSIFICATION OF $h_{FE(1)}$

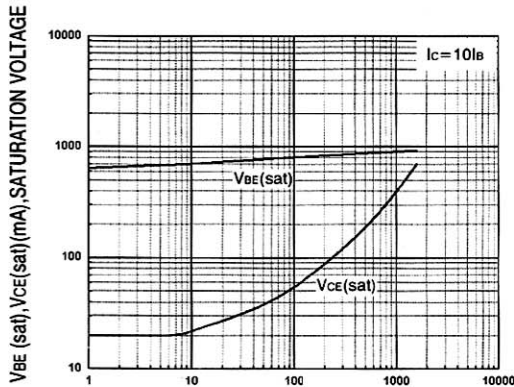
Range	120-200	200-350
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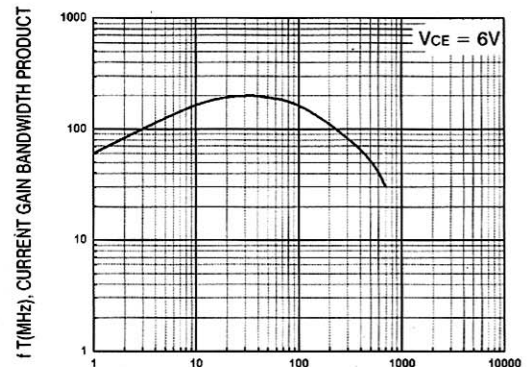
Vce(V), COLLECTOR-EMITTER VOLTAGE
Static Characteristic



Ic (mA), COLLECTOR CURRENT
DC current Gain



Ic (mA), COLLECTOR CURRENT
**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Ic (mA), COLLECTOR CURRENT
Current Gain Bandwidth Product

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)